

## **isc Silicon NPN Power Transistor**

# **BUW34**

### DESCRIPTION

- Collector-Emitter Sustaining Voltage-
  - : V<sub>CEO(SUS)</sub>= 400V(Min.)
- High Speed Switching
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### **APPLICATIONS**

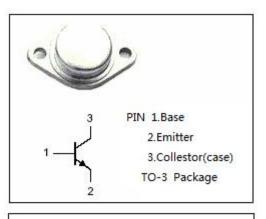
• Designed for high voltage, fast switching applications.

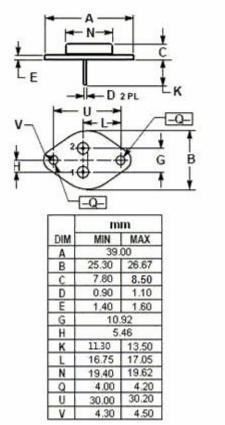
SYMBOL	PARAMETER	VALUE	UNIT				
V <sub>CBO</sub>	Collector-Base Voltage	500	V				
V <sub>CEO</sub>	Collector-Emitter Voltage	400	V				
V <sub>EBO</sub>	Emitter-Base Voltage	7	V				
Ic	Collector Current-Continuous	10	А				
I <sub>CM</sub>	Collector Current-Peak	15	А				
IB	Base Current-Continuous	5	А				
PT	Total Power Dissipation @ T <sub>c</sub> ≤25℃		W				
TJ	Junction Temperature	200	°C				
T <sub>stg</sub>	Storage Temperature Range -65~200		°C				

### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	1.4	°C/W





isc website: www.iscsemi.com



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### ELECTRICAL CHARACTERISTICS

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
Vceo(sus)	Collector-Emitter Sustaining Voltage	I <sub>C</sub> =50mA; I <sub>B</sub> = 0	400			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5Α; I <sub>B</sub> = 1Α			1.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 5Α; I <sub>B</sub> = 1Α			1.5	V
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =7V; I <sub>C</sub> =0			1	mA
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CE</sub> = 500V;V <sub>BE</sub> = 0 V <sub>CE</sub> = 500V;V <sub>BE</sub> = 0; T <sub>C</sub> = 125°C			0.5 3.0	mA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V	15		50	

Switching Times; Resistive Load

t <sub>on</sub>	Turn-On Time		I <sub>C</sub> = 5A; I <sub>B1</sub> = 1A; V <sub>CC</sub> =250V		0.7	μ <b>s</b>
ts	Storage Time		— I <sub>C</sub> = 5A; I <sub>B1</sub> = -I <sub>B2</sub> = 1A; V <sub>CC</sub> =250V		3.0	μs
t <sub>f</sub>	Fall Time				0.8	μs

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